

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

B. Amendments to the Specification.

Please replace the paragraph starting at Page 2, Line 19, with the following.

5 A conventional plasma chamber part cleaning process will now be described with reference to FIG. 5. A conventional chamber part cleaning process 500 may include an initial wet chemical cleaning (step 502). For example, chamber equipment may be submerged in a mixture of hydrogen peroxide (H_2O_2) and ammonium hydroxide (NH_4OH). More particularly, chamber equipment may be submerged in a 30% solution of H_2O_2 in a
10 1:1 ratio with $[NH_4OH]$ NH_4OH for about 20 minutes.

Please replace the paragraph starting at Page 3, Line 8, with the following.

15 A drawback to a conventional method 500 can be how such a cleaning method affects chamber part surfaces. For example, chamber parts can typically be formed from quartz. A wet clean of H_2O_2 and $[NH_4OH]$ NH_4OH may etch quartz surfaces changing surface textures. Changes in chamber part surfaces may result in drift in an etch process, as a changing surface conditions may alter gas flows and or etch chemistry. Further, because cleaning may consume etch chamber parts, such parts may have to be periodically replaced.

20

Please replace the paragraph starting at Page 8, Line 15, with the following.

25 Plasma cleaning with oxygen as a source gas (also referred to "ashing") can remove organic based materials, such a polymer-based photoresist. At the same time, an oxygen plasma etch can leave quartz surfaces essentially unaltered. In this way, unlike conventional cleaning methods that may consume quartz material in an H_2O_2 and $[NH_4OH]$ NH_4OH dip, a third embodiment 300 may clean quartz material with a solvent and/or plasma clean that consumes essentially no quartz material.

30